

Vishay Semiconductors

Hyperfast Rectifier, 2 x 10 A FRED Pt®



TO-220AB



TO-220 FULL-PAK

Base common cathode 02 Common cathode 02 Common cathode 3



VS-30CTH02PbF

VS-30CTH02FPPbF

PRODUCT SUMMARY					
Package	TO-220AB, TO-220FP				
I _{F(AV)}	2 x 15 A				
V_R	200 V				
V _F at I _F	1.05 V				
t _{rr} typ.	See Recovery table				
T _J max.	175 °C				
Diode variation	Common cathode				

FEATURES

- · Hyperfast recovery time
- Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Fully isolated package (V_{INS} = 2500 V_{RMS})
- UL E78996 pending
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 qualified (TO-220)
- Designed and qualified for industrial level (TO-220FP)

DESCRIPTION/APPLICATIONS

200 V series are the state of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control, guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in the output rectification stage of SMPS, UPS, DC/DC converters as well as freewheeling diode in low voltage inverters and chopper motor drives.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Peak repetitive reverse voltage		V_{RRM}		200	V		
	per diode		T _C = 159 °C	- 15 30			
Average rectified forward current	(FULL-PAK) per diode	I _{F(AV)}	T _C = 125 °C		А		
	per device				A		
Non-repetitive peak surge current		I _{FSM}	T _J = 25 °C	200			
Operating junction and storage temperatures		T _J , T _{Stg}		- 65 to 175	°C		

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	Ι _R = 100 μΑ	200	-	-		
Famous de la casa	V_{F}	I _F = 15 A	-	0.92	1.05	V	
Forward voltage		I _F = 15 A, T _J = 125 °C	-	0.78	0.85		
Develope legicome eviment		$V_R = V_R$ rated	-	-	10		
Reverse leakage current I _R		T _J = 125 °C, V _R = V _R rated	-	5	300	μΑ	
Junction capacitance	C _T	V _R = 200 V	-	57	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8	-	nΗ	

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DYNAMIC RECOVERY CHARACTERISTICS (T _C = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	MIN.	TYP.	MAX.	UNITS			
Reverse recovery time		$I_F = 1 A, dI_F/dt = 50$	$I_F = 1 \text{ A}, dI_F/dt = 50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	35			
	t _{rr}	$I_F = 1 \text{ A, } dI_F/dt = 100 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		-	-	30			
		T _J = 25 °C	$I_F = 15 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_B = 160 \text{ V}$	-	26	-	ns A		
		T _J = 125 °C		-	40	-			
Dook roopyon/ ourront	I _{RRM}	T _J = 25 °C		-	2.8	-			
Peak recovery current		T _J = 125 °C	-11	-	6.0	-			
Reverse recovery charge	Q _{rr}	T _J = 25 °C		-	37	-	nC		
		T _J = 125 °C		-	120	-			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction ar temperature range	nd storage	T _J , T _{Stg}		- 65	-	175	°C		
Thermal resistance, per diode		Б	Mounting surface, flat, smooth	-	-	1.1	°C/W		
junction to case	(FULL-PAK) per diode	- R _{thJC}	and greased	-	-	3.5	C/VV		
Marking device			Case style TO-220AB	30CTH02					
			Case style TO-220 FULL-PAK		30CTI	H02FP			

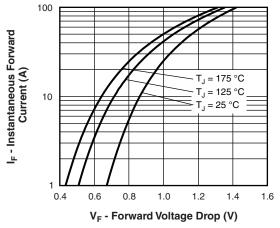


Fig. 1 - Typical Forward Voltage Drop Characteristics

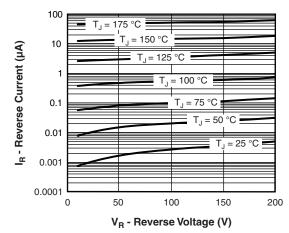


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



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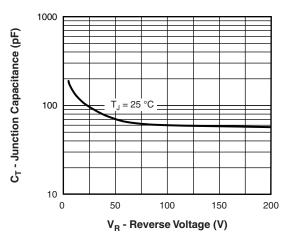


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

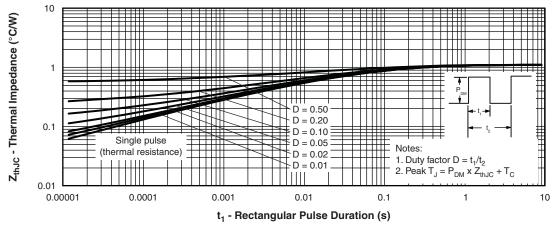


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

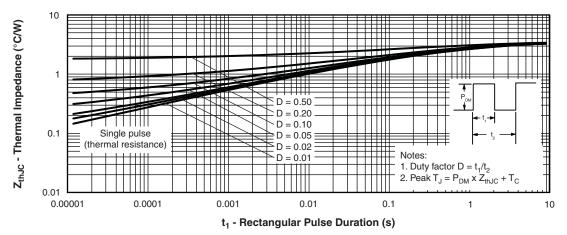


Fig. 5 - Maximum Thermal Impedance Z_{thJC} Characteristics (FULL-PAK)

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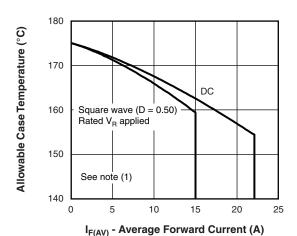


Fig. 6 - Maximum Allowable Case Temperature vs. Average Forward Current

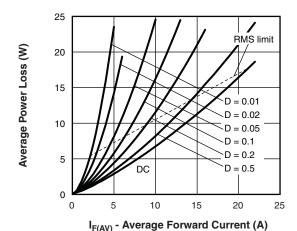


Fig. 8 - Forward Power Loss Characteristics

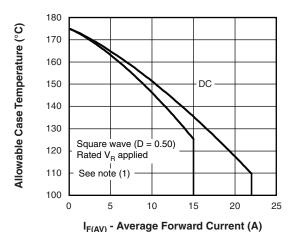


Fig. 7 - Maximum Allowable Case Temperature vs. Average Forward Current (FULL-PAK)

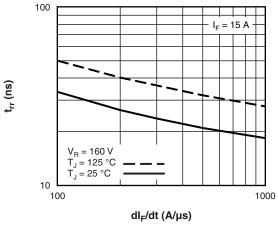


Fig. 9 - Typical Reverse Recovery Time vs. dI_F/dt

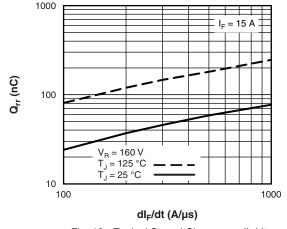


Fig. 10 - Typical Stored Charge vs. dI_F/dt

Note

(1) Formula used: T_C = T_J - (Pd + Pd_{REV}) x R_{thJC}; Pd = Forward power loss = I_{F(AV)} x V_{FM} at (I_{F(AV)}/D) (see fig. 8); Pd_{REV} = Inverse power loss = V_{R1} x I_R (1 - D); I_R at V_{R1} = Rated V_R



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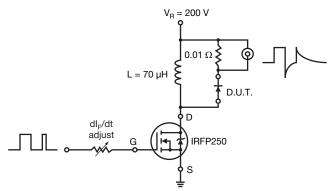
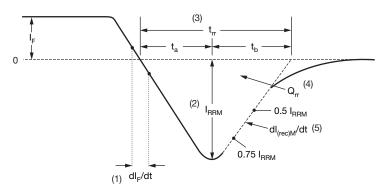


Fig. 11 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) Q_{rr} area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 12 - Reverse Recovery Waveform and Definitions

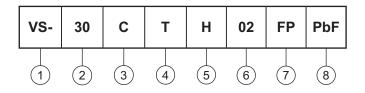
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ORDERING INFORMATION TABLE

Device code



Vishay Semiconductors product

Current rating (30 = 30 A)

C = Common cathode

T = TO-220

H = Hyperfast recovery

Voltage rating (02 = 200 V)

• None = TO-220AB

• FP = TO-220 FULL-PAK

8 PbF = Lead (Pb)-free

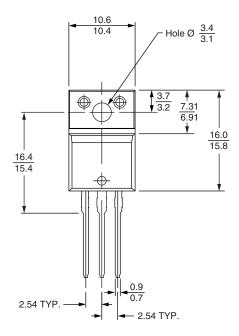
Tube standard pack quantity: 50 pieces

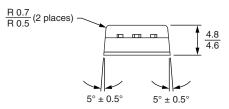
LINKS TO RELATED DOCUMENTS					
Dimensions	TO-220AB	www.vishay.com/doc?95222			
Dimensions	TO-220AB FULL-PAK	www.vishay.com/doc?95072			
Dest enabling information	TO-220AB	www.vishay.com/doc?95225			
Part marking information	TO-220AB FULL-PAK	www.vishay.com/doc?95069			

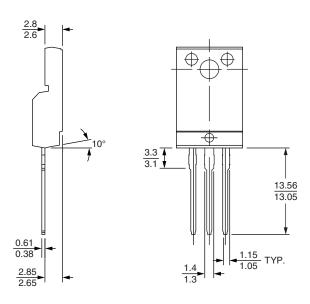


Vishay Semiconductors

DIMENSIONS in millimeters







Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220 FULL-PAK



Vishay Semiconductors

TO-220AB

DIMENSIONS in millimeters and inches



Lead assignments

Diodes

- 1. Anode/open
- 2. Cathode
- 3. Anode

Conforms to JEDEC outline TO-220AB

SYMBOL	MILLIN	IETERS	INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
Α	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
С	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIM	IETERS	INC	HES	NOTES
STIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
е	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	6.09	6.48	0.240	0.255	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
ØΡ	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		
		•	•	•	

Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- (2) Lead dimension and finish uncontrolled in L1
- (3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Dimension b1, b3 and c1 apply to base metal only
- (5) Controlling dimensions: inches
- (6) Thermal pad contour optional within dimensions E, H1, D2 and E1
- (7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed
- (8) Outline conforms to JEDEC TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

Lead tip





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